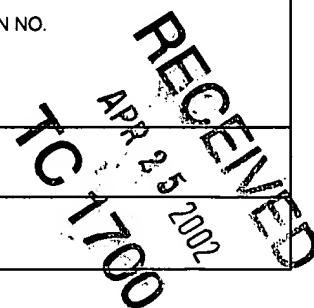
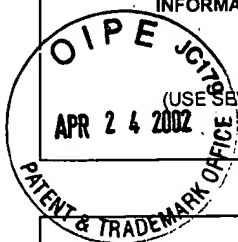


FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMMC.030AUSAPPLICATION NO.
09/801,542INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Bondestam et al.FILING DATE
March 7, 2001GROUP
1763

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
W	4,222,576	9/16/80	Clements	—	—	
	4,889,319	12/26/89	Phillips et al.	—	—	
	5,314,574	5/24/94	Takahashi	—	—	
	5,520,743	5/28/96	Takahashi	—	—	
	5,709,757	1/20/98	Hatano et al.	—	—	
	5,885,353	3/23/99	Strodtbeck et al.	—	—	
	5,891,251	4/6/99	MacLeish et al.	—	—	
	6,054,688	4/25/00	Moschini	—	—	
	6,120,609	9/19/00	Selyutin et al.	—	—	
	6,125,859	10/3/00	Kao et al.	—	—	
	6,174,377 B1	1/16/01	Doering et al.	—	—	
	6,350,319 B1	2/26/02	Curtis et al.	—	—	
W	US 2001/0035127 A1	11/1/01	Metzner et al.	—	—	

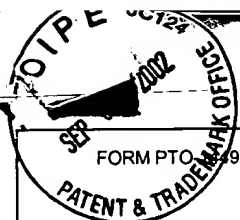
FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

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EXAMINER	<i>W. M. Moore</i>	DATE CONSIDERED	11/7/02
<p>*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.</p>			



FORM PTO-1009

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMMC.030AUSAPPLICATION NO.
09/801,542SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Bondestam et al.FILING DATE
March 7, 2001GROUP
1763

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
WA	6,306,216 B1	10/23/01	Kim et al.	—	—	

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TC 1700EXAMINER *W. S. Munn*DATE CONSIDERED *11/7/02*

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
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ASMMC.030AUSAPPLICATION NO.
09/801,542INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Bondestam et al.FILING DATE
March 7, 2001GROUP
Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
wn	1	4,058,430	11/15/77	Suntola et al.	156	611	11/25/75
	2	4,389,973	06/28/83	Suntola et al.	118	725	12/11/81
	3	4,413,022	11/01/83	Suntola et al.	427	255.2	06/21/79
	4	4,747,367	05/31/88	Posa	118	715	06/12/86
	5	4,761,269	08/02/88	Conger et al.	422	245	06/12/86
	6	4,836,138	06/06/89	Robinson et al.	118	666	06/18/87
	7	4,993,357	02/19/91	Scholz	118	715	12/21/89
	8	5,071,670	12/10/91	Kelly	427	38	06/11/90
	9	5,281,274	01/25/94	Yoder	118	697	02/04/93
	10	5,294,572	03/15/94	Granneman et al.	437	225	07/21/93
	11	5,306,666	04/26/94	Izumi	437	192	07/21/93
	12	5,711,811	01/27/98	Suntola et al.	118	711	06/23/98
	13	5,769,950	06/23/98	Takasu et al.	118	715	06/23/98
	14	5,855,680	01/05/99	Soininen et al.	118	719	01/21/98
	15	5,879,415	03/09/99	Shimada	29	25.01	08/16/96
	16	5,916,365	06/29/99	Sherman	117	92	08/16/96
	17	6,015,590	01/18/00	Suntola et al.	427	255.23	09/07/99
	18	6,042,652	03/28/00	Hyun et al.	118	719	09/07/99
wn	19	US 6,167,834 B1	01/02/01	Wang et al.	118	723 E	08/13/92

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
wn	20	WO 96/17107	06.06.96	PCT	1	1		
wn	21	WO 00/40772	13.07.00	PCT	1	1		
wn	22	WO 00/47404	17.08.00	PCT	1	1		

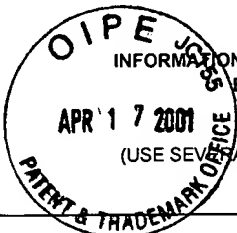
EXAMINER

Wes Munn

DATE CONSIDERED

11/7/02

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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMMC.030AUS	APPLICATION NO. 09/801,542
		APPLICANT Bondestam et al.	
		FILING DATE March 7, 2001	GROUP Unknown

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
Wm	23	B. Abeles et al., "Amorphous Semiconductor Superlattices," <u>Physical Review Letters</u> , Vol. 51, No. 21, pp. 2003-2006 (November 1983). ✓
	24	C. Döscö et al., "Deposition of Tin Oxide into Porous Silicon by Atomic Layer Epitaxy," <u>J. Electrochem. Soc.</u> , Vol. 143, No. 2, pp. 683-687 (February 1996). ✓
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	29	K. Kukli et al., "Influence of atomic layer deposition parameters on the phase content of Ta ₂ O ₅ films," <u>Journal of Crystal Growth</u> , Vol. 212, pp. 459-468 (2000). ✓
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	31	P. Martenson et al., "Use of Atomic Layer Epitaxy for fabrication of Si/TiN/Cu Structures," <u>J. Vac. Sci. Technol. B</u> , Vol. 17, No. 5, pp. 2122-2128 (September/October 1999). ✓
	32	J. Min et al., "Atomic Layer Deposition of TiN Thin Films by Sequential Introduction of Ti Precursor and NH ₃ ," <u>Mat. Res. Soc. Proc.</u> , Vol. 514, pp. 337-342 (1998). ✓
	33	J. Min et al., "Atomic Layer Deposition of TiN Films by Alternate Supply of Tetrakis (ethylmethylamino) - Titanium and Ammonia, <u>Jpn. J. Appl. Phys.</u> , Vol. 37, Part 1, No. 9A, pp. 4999-5004 (September 1998). ✓
	34	L. Niinistö et al., "Synthesis of Oxide Thin Films and Overlayers by Atomic Layer Epitaxy for Advanced Applications," <u>Materials Science and Engineering</u> , Vol. B41, pp. 23-29 (1996). ✓
	35	M. Putkonen, "Surface-controlled growth of magnesium oxide thin films by atomic layer epitaxy," <u>Journal of Materials Chemistry</u> , Vol. 9, pp. 2449-2452 (1999). ✓
	36	J. Rautanen et al., "The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy," <u>Applied Surface Science</u> , Vols. 82/83, pp. 553-558 (1994). ✓
	37	M. Ritala et al., "Atomic Layer Epitaxy Growth of TiN Thin Films from TiI ₄ and NH ₃ ," <u>J. Electrochem. Soc.</u> , Vol. 145, No. 8, pp. 2914-2920 (August 1998). ✓
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	42	T. Suntola, "Atomic Layer Epitaxy," <u>Materials Science Reports</u> 4, pp. 261-312 (1989). ✓
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	44	H. Virola et al., "Controlled growth of tin dioxide thin film by atomic layer epitaxy," <u>Thin Solid Films</u> , Vol. 249, pp. 144-149 (1994). ✓
Wm	45	M. Wise et al., "Diethyldiethoxysilane as a New Precursor for SiO ₂ Growth on Silicon," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 334, pp. 37-43 (1994). ✓
	46	Merkku-Ylämaki et al., "Luku VII. Ohutkalvotekniikka," <u>Työteknikka</u>, pp. 253-261 (1986). ✓

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EXAMINER Wm	DATE CONSIDERED 11/7/02
<p>*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.</p>	